



IRL3103D1PBF Information



For Reference Only

Part Number IRL3103D1PBF

Manufacturer Infineon Technologies

Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 30V 64A TO-220AB

Package TO-220-3

Category

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









IRL3103D1PBF Specifications

Manufacturer Part NumberIRL3103D1PBFManufacturerInfineon TechnologiesCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-220-3SeriesFETKY?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C64A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id1V @ 250µAGate Charge (Qg) (Max) @ Vgs43nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds1900pF @ 25VVgs (Max)±16VFET Feature-Power Dissipation (Max)2W (Ta), 89W (Tc)Rds On (Max) @ Id, Vgs14 mOhm @ 34A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3Report errors?		
Category Discrete Semiconductor Products Package TO-220-3 Series FETKY? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 64A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 1V @ 250μA Gate Charge (Qg) (Max) @ Vgs 43nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 1900pF @ 25V Vgs (Max) ±16V FET Feature - Power Dissipation (Max) 2W (Ta), 89W (Tc) Rds On (Max) @ Id, Vgs 14 mOhm @ 34A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Manufacturer Part Number	IRL3103D1PBF
Package TO-220-3 Series FETKY? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 64A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 1V @ 250μA Gate Charge (Qg) (Max) @ Vgs 43nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 1900pF @ 25V Vgs (Max) ±16V FET Feature - Power Dissipation (Max) 2W (Ta), 89W (Tc) Rds On (Max) @ Id, Vgs 14 mOhm @ 34A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Manufacturer	Infineon Technologies
Package TO-220-3 Series FETKY? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 64A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 1V @ 250μA Gate Charge (Qg) (Max) @ Vgs 43nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 1900pF @ 25V Vgs (Max) ±16V FET Feature - Power Dissipation (Max) 2W (Ta), 89W (Tc) Rds On (Max) @ Id, Vgs 14 mOhm @ 34A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Category	Discrete Semiconductor Products
Series FETKY? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 64A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 1V @ 250µA Gate Charge (Qg) (Max) @ Vgs 43nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 1900pF @ 25V Vgs (Max) ±16V FET Feature - Power Dissipation (Max) 2W (Ta), 89W (Tc) Rds On (Max) @ Id, Vgs 14 mOhm @ 34A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C64A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id1V @ 250μAGate Charge (Qg) (Max) @ Vgs43nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds1900pF @ 25VVgs (Max)±16VFET Feature-Power Dissipation (Max)2W (Ta), 89W (Tc)Rds On (Max) @ Id, Vgs14 mOhm @ 34A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Package	TO-220-3
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 64A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 14 mOhm @ 34A, 10V Operating Temperature Supplier Device Package Package / Case MOSFET (Metal Oxide) 30V MOSFET (Metal Oxide) 30V 20V 44 TC) 64A (Tc) 64B (Textanal particular p	Series	FETKY?
Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C64A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id1V @ 250μAGate Charge (Qg) (Max) @ Vgs43nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds1900pF @ 25VVgs (Max)±16VFET Feature-Power Dissipation (Max)2W (Ta), 89W (Tc)Rds On (Max) @ Id, Vgs14 mOhm @ 34A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 14 mOhm @ 34A, 10V Operating Temperature Supplier Device Package Package / Case 64A (Tc) 64B (Fixed and point	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 1V @ 250μA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 14 mOhm @ 34A, 10V Operating Temperature Supplier Device Package Package / Case TO-220AB TO-220-3	Drain to Source Voltage (Vdss)	30V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 14 mOhm @ 34A, 10V Operating Temperature Supplier Device Package Package / Case 1V @ 250μA 1900pF @ 25V 1900pF @ 25V 2W (Ta), 89W (Tc) 14 mOhm @ 34A, 10V Through Hole TO-220AB TO-220-3	Current - Continuous Drain (Id) @ 25°C	64A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 1900pF @ 25V Vgs (Max) ±16V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 14 mOhm @ 34A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case TO-220AB TO-220-3	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±16V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 14 mOhm @ 34A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Vgs(th) (Max) @ Id	1V @ 250μA
Vgs (Max) ±16V FET Feature - Power Dissipation (Max) 2W (Ta), 89W (Tc) Rds On (Max) @ Id, Vgs 14 mOhm @ 34A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Gate Charge (Qg) (Max) @ Vgs	43nC @ 4.5V
FET Feature - Power Dissipation (Max) 2W (Ta), 89W (Tc) Rds On (Max) @ Id, Vgs 14 mOhm @ 34A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Input Capacitance (Ciss) (Max) @ Vds	1900pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 14 mOhm @ 34A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Vgs (Max)	±16V
Rds On (Max) @ Id, Vgs14 mOhm @ 34A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Power Dissipation (Max)	2W (Ta), 89W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	14 mOhm @ 34A, 10V
Supplier Device Package TO-220AB Package / Case TO-220-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	TO-220AB
Report errors?	Package / Case	TO-220-3
		Report errors?

IRL3103D1PBF Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRL3103D1PBF Payment Methods



















IRL3103D1PBF Shipping Methods













If you have any question about IRL3103D1PBF, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com